STP12NM50 - STP12NM50FP
STB12NM50 - STB12NM50-1

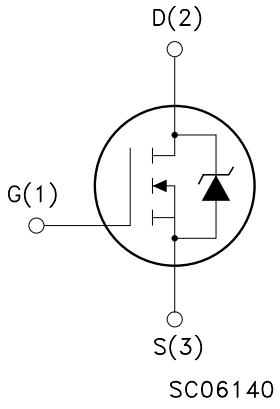
N-channel 550V @ tjmax - 0.30Ω - 12A TO-220/FP/D²/I²PAK
MDmesh™ Power MOSFET

General features

Type	V_{DSS} (@Tjmax)	$R_{DS(on)}$	I_D
STB12NM50	550V	<0.35Ω	12A
STB12NM50-1	550V	<0.35Ω	12A
STP12NM50	550V	<0.35Ω	12A
STP12NM50FP	550V	<0.35Ω	12A

- High dv/dt and avalanche capabilities
- Low input capacitance and gate charge
- 100% avalanche tested
- Low gate input resistance
- Tight process control and high manufacturing yields

Internal schematic diagram



Description

The MDmesh™ is a new revolutionary MOSFET technology that associates the Multiple Drain process with the Company's PowerMESH™ horizontal layout. The resulting product has an outstanding low on-resistance, impressively high dv/dt and excellent avalanche characteristics. The adoption of the Company's proprietary strip technique yields overall dynamic performance that is significantly better than that of similar competition's products.

Applications

- Switching application

Order codes

Part number	Marking	Package	Packaging
STB12NM50T4	B12NM50	D²PAK	Tape & reel
STB12NM50-1	B12NM50	I²PAK	Tube
STP12NM50	P12NM50	TO-220	Tube
STP12NM50FP	P12NM50FP	TO-220FP	Tube

Contents

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value		Unit
		TO-220-/D²PAK/I²PAK	TO-220FP	
V_{GS}	Gate-source voltage	± 30		V
I_D	Drain current (continuous) at T_C = 25°C	12	12(1)	A
I_D	Drain current (continuous) at T_C=100°C	7.5	7.5(1)	A
I_{DM}(2)	Drain current (pulsed)	48	48(1)	A
P_{TOT}	Total dissipation at T_C = 25°C	160	35	W
	Derating Factor	1.28	0.28	W/°C
V_{ISO}	Insulation winthstand voltage (DC)	--	2500	V
dv/dt(3)	Peak diode recovery voltage slope	15		V/ns
T_J T_{stg}	Operating junction temperature Storage temperature	-65 to 150		°C

1. Limited only by maximum temperature allowed
2. Pulse width limited by safe operating area
3. $I_{SD} \leq 12A$, di/dt ≤400A/µs, V_{DD} =80%$V_{(BR)DSS}$

Table 2. Thermal data

Symbol	Parameter	Value		Unit
		TO-220/D²PAK/ I² PAK	TO-220FP	
$R_{thj\text{-}case}$	Thermal resistance junction-case Max	0.78	3.57	°C/W
$R_{thj\text{-}a}$	Thermal resistance junction-ambient Max	62.5		°C/W
T_l	Maximum lead temperature for soldering purpose	300		°C

Table 3. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AS}	Avalanche current, repetitive or not-repetitive (pulse width limited by Tj Max)	6	A
E_{AS}	Single pulse avalanche energy (starting Tj=25°C, Id=Iar, Vdd=50V)	400	mJ

2 Electrical characteristics

(T_{CASE}=25°C unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	I_D = 250 µA, V_{GS}= 0	500			V
I_{DSS}	Zero gate voltage drain current (V_{GS} = 0)	V_{DS} = Max rating, V_{DS} = Max rating @125°C			1 10	µA µA
I_{GSS}	Gate body leakage current (V_{DS} = 0)	V_{GS} = ±30V			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	V_{DS}= V_{GS}, I_D = 50µA	3	4	5	V
$R_{DS(on)}$	Static drain-source on resistance	V_{GS}= 10V, I_D= 6A		0.30	0.35	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
g_{fs} (1)	Forward transconductance	V_{DS} =15V, I_D = 6A		5.5		S
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	V_{DS} =25V, f=1 MHz, V_{GS}=0		1000 250 20		pF pF pF
$C_{oss\ eq}$ (2).	Equivalent output capacitance	V_{GS}=0, V_{DS} =0V to 400V		90		pF
$t_{d(on)}$ t_r	Turn-on Delay Time Rise Time	V_{DD} = 250V, I_D = 6A, R_G = 4.7Ω, V_{GS} = 10V (see Figure 14)		20 10		ns ns
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	V_{DD}=400V, I_D = 12A V_{GS} =10V (see Figure 15)		28 8 18	39	nC nC nC
R_g	Gate input resistance	f=1MHz Gate DC Bias=0 test signal level=20mV open drain		1.6		Ω

1. Pulsed: pulse duration=300µs, duty cycle 1.5%
2. $C_{oss\ eq.}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} inceases from 0 to 80% V_{DSS}

Table 6. Source drain diode

Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
I_{SD}	Source-drain current				11	A
I_{SDM}(1)	Source-drain current (pulsed)				48	A
V_{SD}(2)	Forward on voltage	I_{SD}=12A, V_{GS}=0			1.5	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	I_{SD}=12A, di/dt = 100A/µs, V_{DD}=100V, Tj=25°C (see Figure 16)		270 2.23 16.5		ns µC A
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	I_{SD}=12A, di/dt = 100A/µs, V_{DD}=100V, Tj=150°C (see Figure 16)		340 3 18		ns µC A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration=300µs, duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

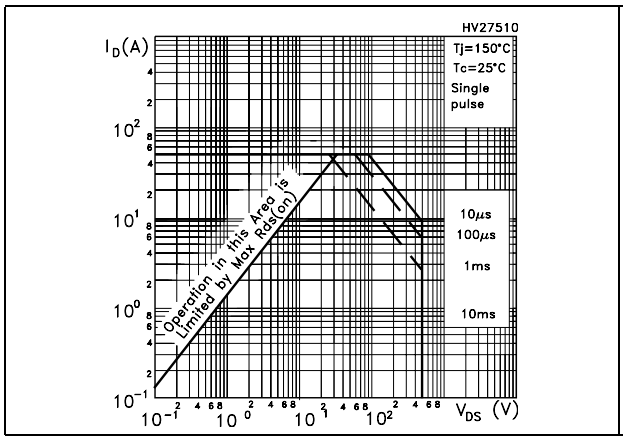


Figure 2. Thermal impedance

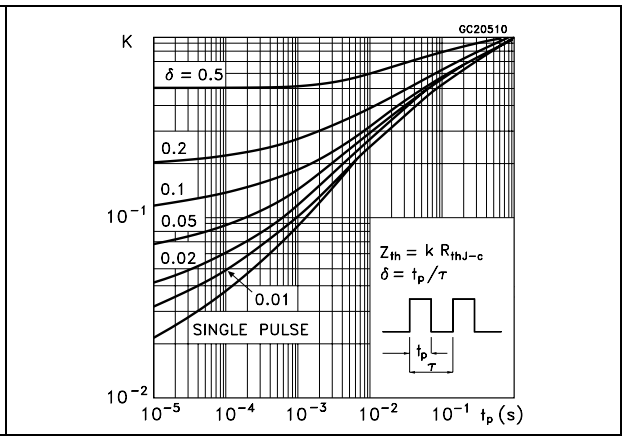


Figure 3. Safe operating area for TO-220FP

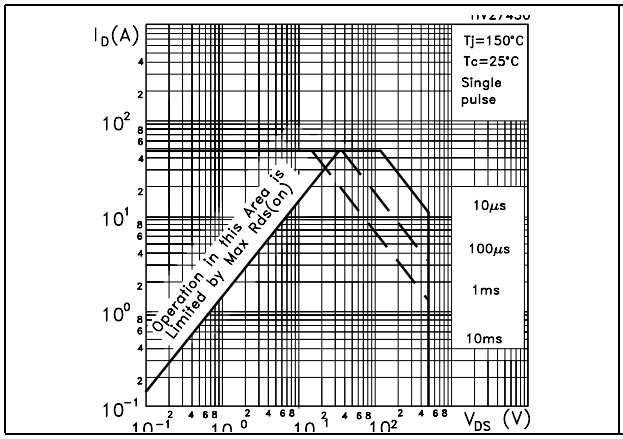


Figure 4. Thermal impedance for TO-220FP

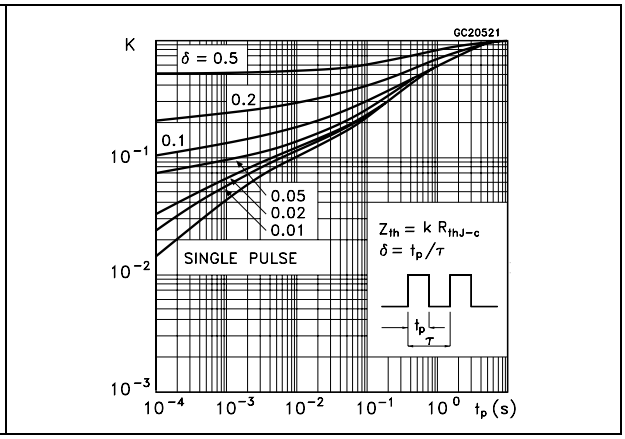


Figure 5. Output characterisics

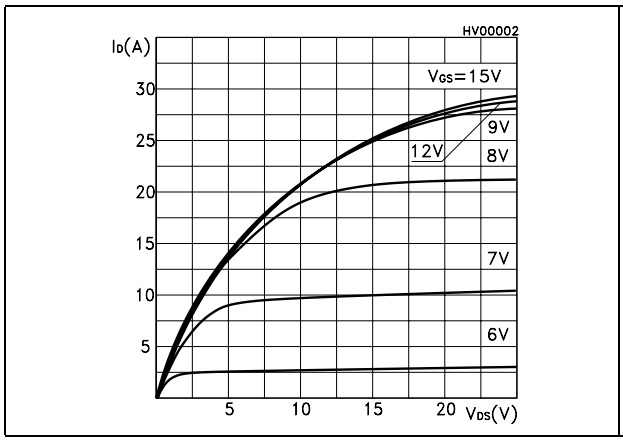


Figure 6. Transfer characteristics

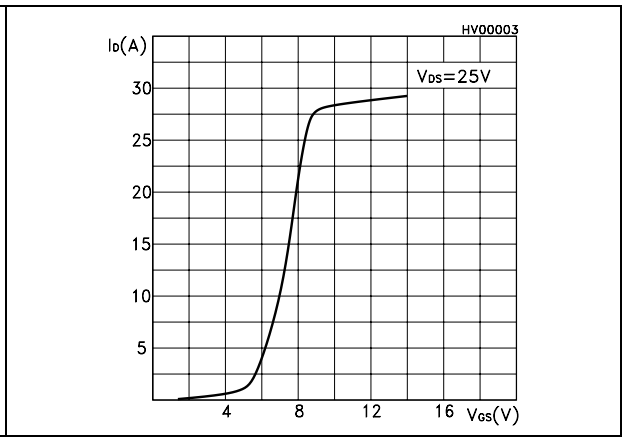


Figure 7. Transconductance

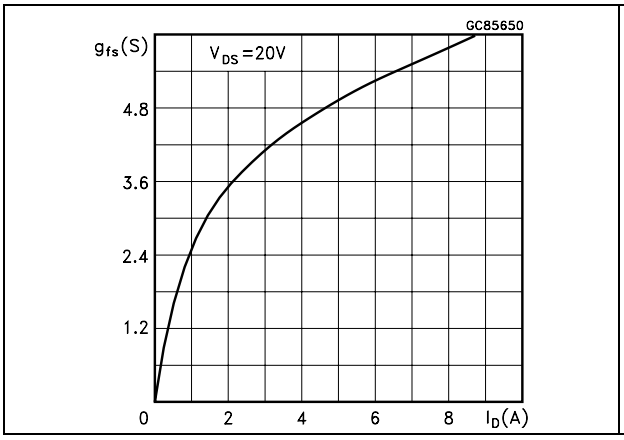


Figure 8. Static drain-source on resistance

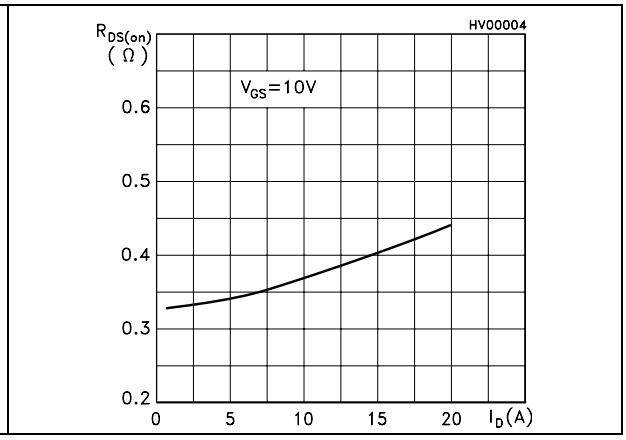


Figure 9. Gate charge vs gate-source voltage

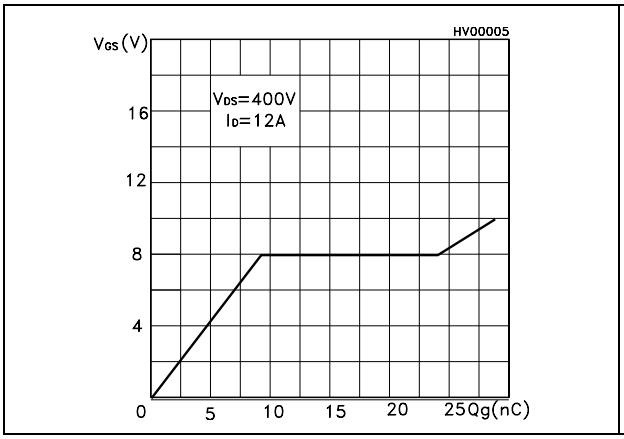


Figure 10. Capacitance variations

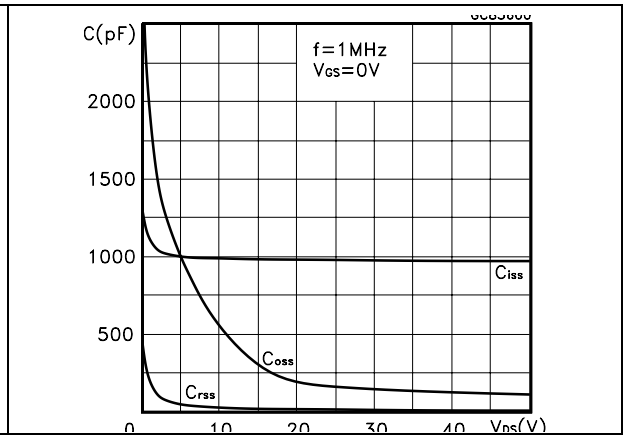


Figure 11. Normalized gate threshold voltage vs temperature

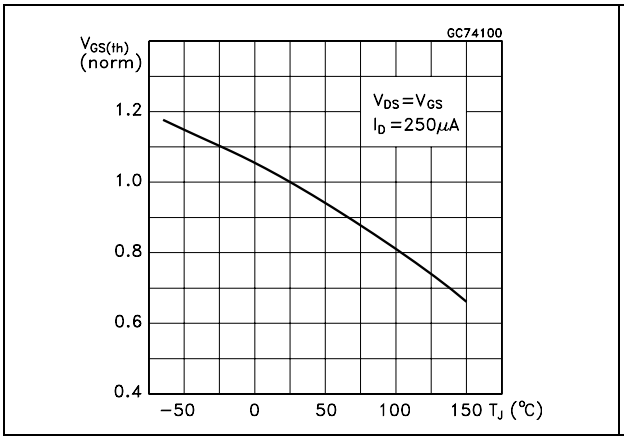


Figure 12. Normalized on resistance vs temperature

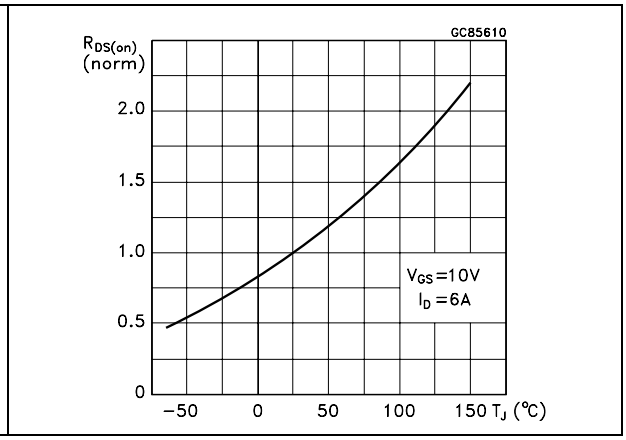
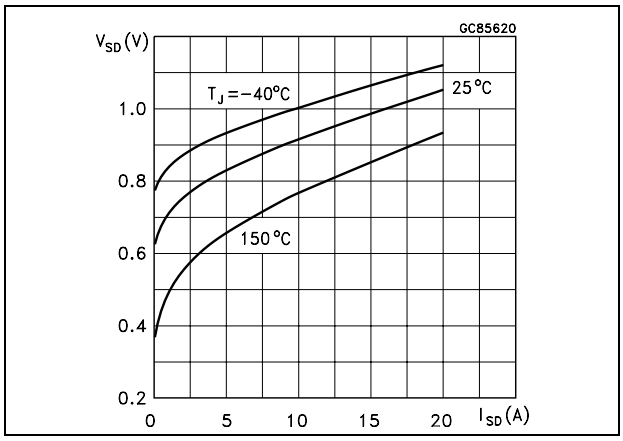


Figure 13. Source-drain diode forward characteristics



3 Test circuit

Figure 14. Switching times test circuit for resistive load

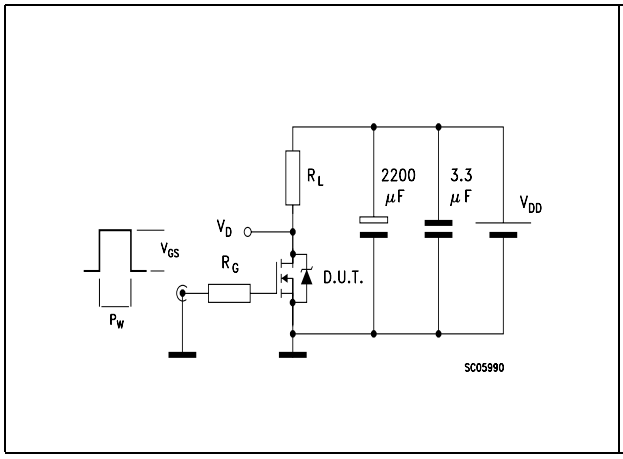


Figure 15. Gate charge test circuit

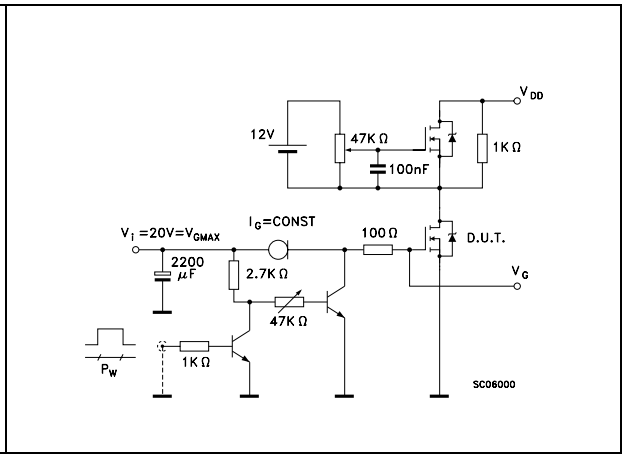


Figure 16. Test circuit for inductive load switching and diode recovery times

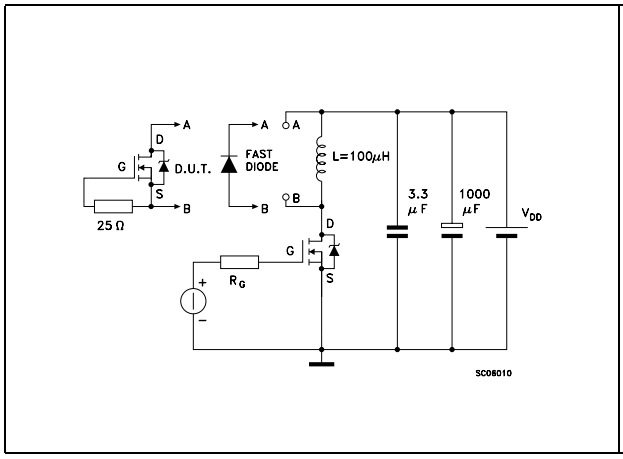


Figure 17. Unclamped Inductive load test circuit

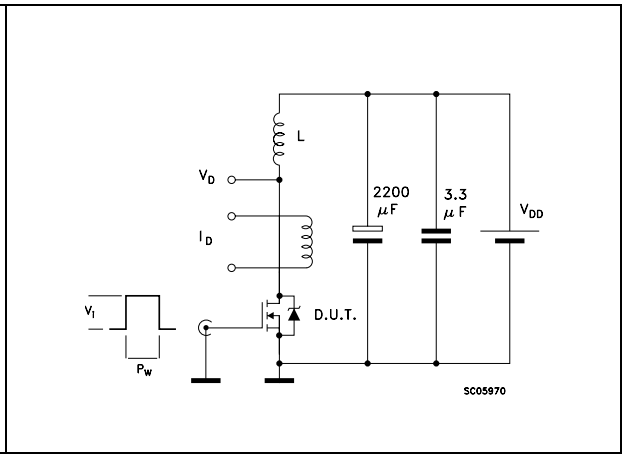


Figure 18. Unclamped inductive waveform

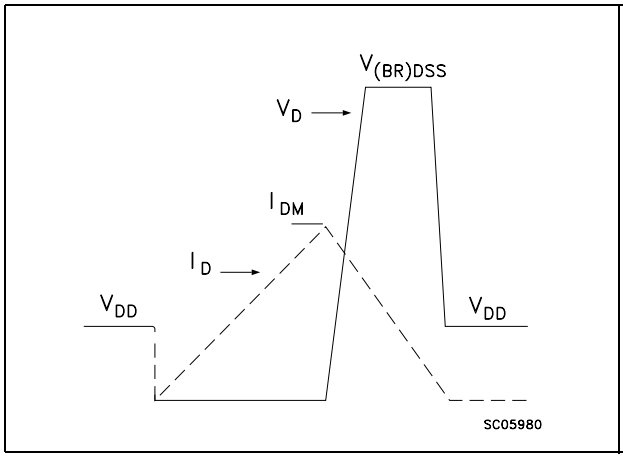
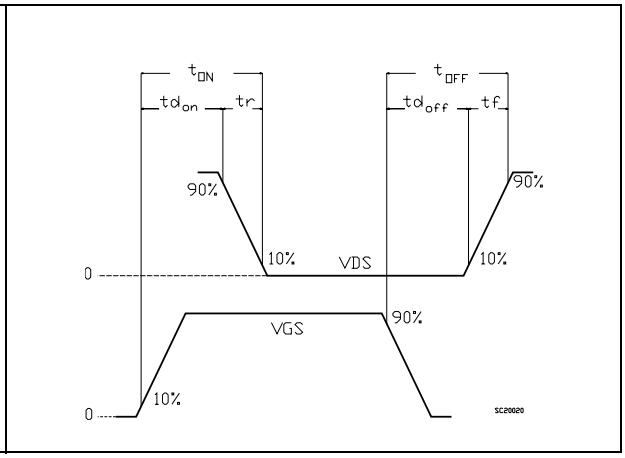


Figure 19. Switching time waveform

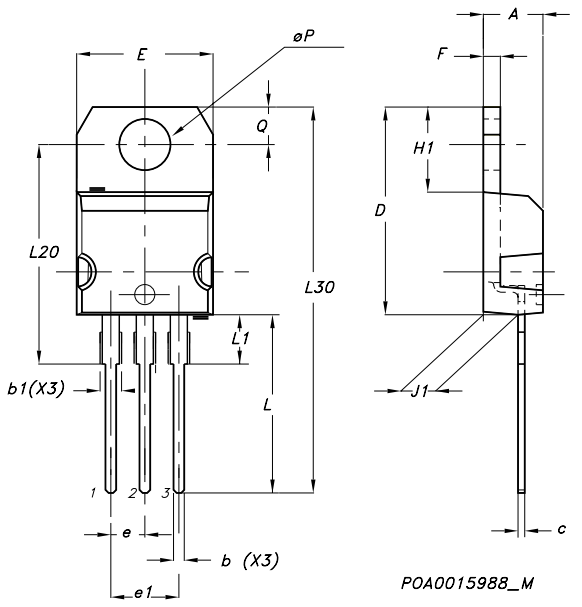


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

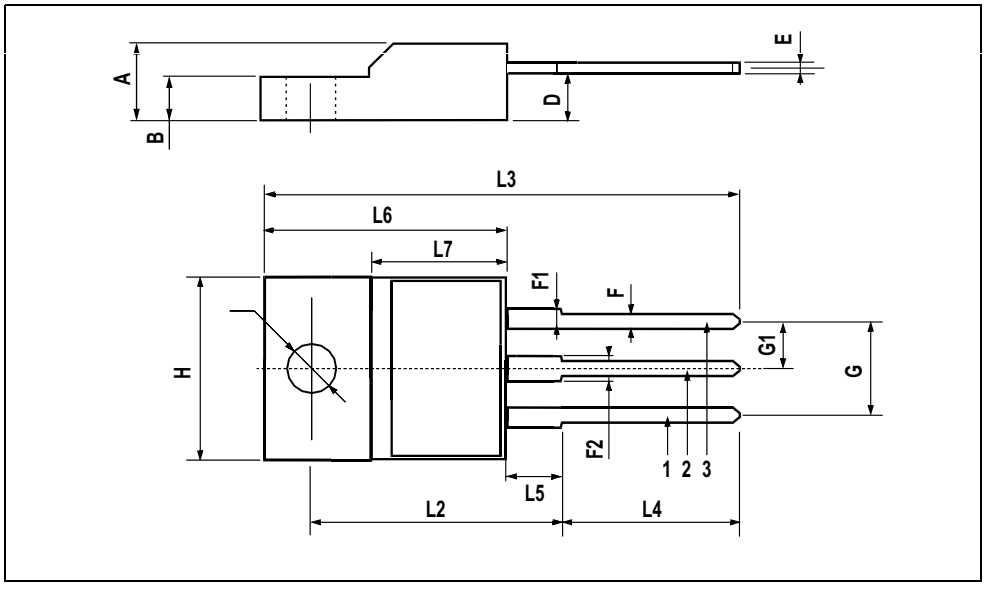
TO-220 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.15		1.70	0.045		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.60		0.620
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.052
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
øP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



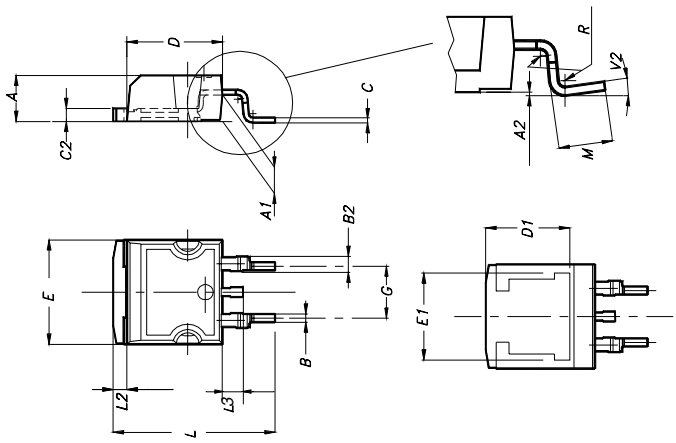
TO-220FP MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	.0385		0.417
L5	2.9		3.6	0.114		0.141
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



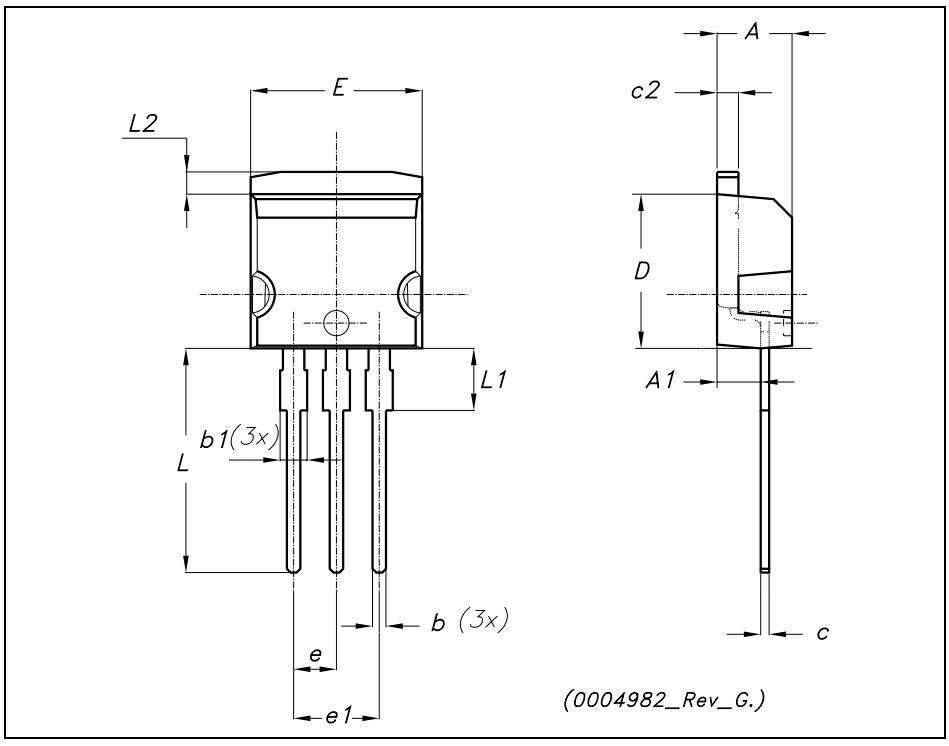
D^2PAK MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0º		4º			



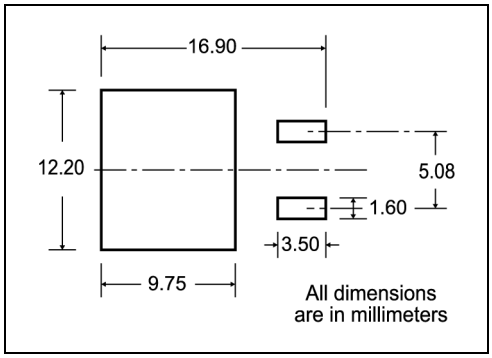
TO-262 (I^2PAK) MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
A1	2.40		2.72	0.094		0.107
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.49		0.70	0.019		0.027
c2	1.23		1.32	0.048		0.052
D	8.95		9.35	0.352		0.368
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
E	10		10.40	0.393		0.410
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L2	1.27		1.40	0.050		0.055

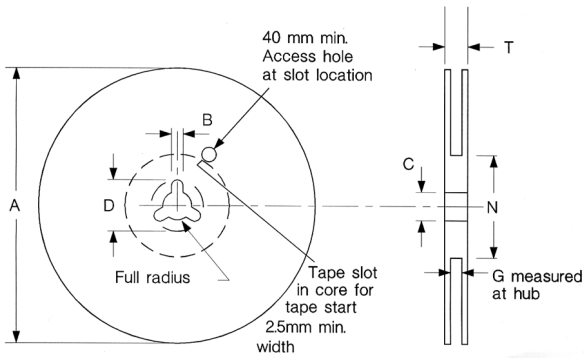


5 Packaging mechanical data

D²PAK FOOTPRINT



TAPE AND REEL SHIPMENT



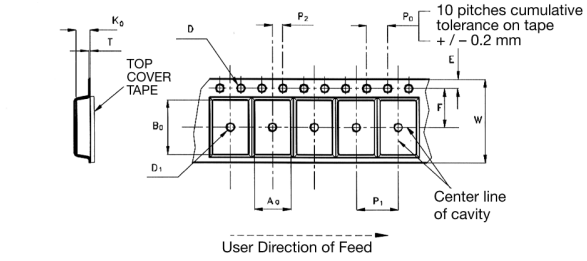
REEL MECHANICAL DATA

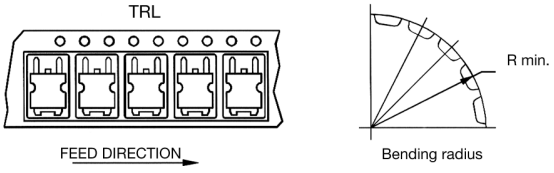
DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0795	
G	24.4	26.4	0.960	1.039
N	100		3.937	
T		30.4		1.197

BASE QTY	BULK QTY
1000	1000

TAPE MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	10.5	10.7	0.413	0.421
B0	15.7	15.9	0.618	0.626
D	1.5	1.6	0.059	0.063
D1	1.59	1.61	0.062	0.063
E	1.65	1.85	0.065	0.073
F	11.4	11.6	0.449	0.456
K0	4.8	5.0	0.189	0.197
P0	3.9	4.1	0.153	0.161
P1	11.9	12.1	0.468	0.476
P2	1.9	2.1	0.075	0.082
R	50		1.574	
T	0.25	0.35	0.0098	0.0137
W	23.7	24.3	0.933	0.956





* on sales type

6 Revision history

Table 7. Revision history

Date	Revision	Changes
14-Mar-2004	8	Preliminary version
15-Feb-2006	9	New voltage value on first page at tjmax.
05-Apr-2006	10	Inserted ecopack indication
27-Jul-2006	11	New template, no content change

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